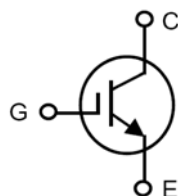


**High Voltage XPT™  
IGBT**
**IXYX40N450HV**

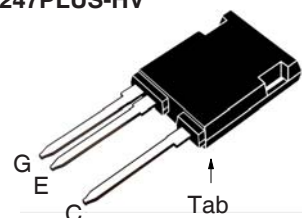
$$V_{CES} = 4500V$$

$$I_{C110} = 40A$$

$$V_{CE(sat)} \leq 3.9V$$



Symbol	Test Conditions	Maximum Ratings	
$V_{CES}$	$T_C = 25^\circ C$ to $150^\circ C$	4500	V
$V_{CGR}$	$T_J = 25^\circ C$ to $150^\circ C$ , $R_{GE} = 1M\Omega$	4500	V
$V_{GES}$	Continuous	$\pm 20$	V
$V_{GEM}$	Transient	$\pm 30$	V
$I_{C25}$	$T_C = 25^\circ C$	95	A
$I_{C110}$	$T_C = 110^\circ C$	40	A
$I_{CM}$	$T_C = 25^\circ C$ , 1ms	350	A
<b>SSOA (RBSOA)</b>	$V_{GE} = 15V$ , $T_{VJ} = 125^\circ C$ , $R_G = 10\Omega$	$I_{CM} = 120$	A
	Clamped Inductive Load	3600	V
$P_C$	$T_C = 25^\circ C$	660	W
$T_J$		-55 ... +150	$^\circ C$
$T_{JM}$		150	$^\circ C$
$T_{stg}$		-55 ... +150	$^\circ C$
$T_L$	Maximum Lead Temperature for Soldering	300	$^\circ C$
$T_{SOLD}$	1.6 mm (0.062in.) from Case for 10s	260	$^\circ C$
$F_C$	Mounting Force	20..120/4.5..27	N/lb
<b>Weight</b>		6	g

**TO-247PLUS-HV**


G = Gate                      E = Emitter  
C = Collector                Tab = Collector

**Features**

- High Voltage Package
- High Blocking Voltage
- High Peak Current Capability
- Low Saturation Voltage

**Advantages**

- Low Gate Drive Requirement
- High Power Density

**Applications**

- Switch-Mode and Resonant-Mode Power Supplies
- Uninterruptible Power Supplies (UPS)
- Laser Generators
- Capacitor Discharge Circuits
- AC Switches

Symbol	Test Conditions ( $T_J = 25^\circ C$ Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$BV_{CES}$	$I_C = 250\mu A$ , $V_{GE} = 0V$	4500		V
$V_{GE(th)}$	$I_C = 250\mu A$ , $V_{CE} = V_{GE}$	3.0		5.0 V
$I_{CES}$	$V_{CE} = V_{CES}$ , $V_{GE} = 0V$			25 $\mu A$ 1.25 mA
	$T_J = 125^\circ C$			
$I_{GES}$	$V_{CE} = 0V$ , $V_{GE} = \pm 20V$			$\pm 200$ nA
$V_{CE(sat)}$	$I_C = 40A$ , $V_{GE} = 15V$ , Note 1		3.2	3.9 V
	$T_J = 125^\circ C$		4.0	V

### Symbol Test Conditions

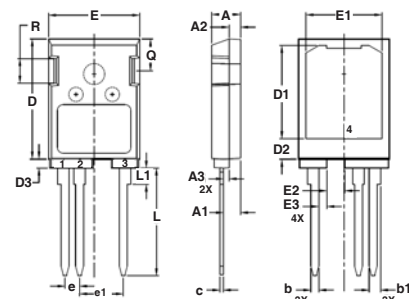
( $T_J = 25^\circ\text{C}$  Unless Otherwise Specified)

### Characteristic Values

		Min.	Typ.	Max.	
$g_{fs}$	$I_C = 40\text{A}, V_{CE} = 10\text{V}$ , Note 1	18	30		S
$C_{ies}$	$V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$		3550		pF
$C_{oes}$			146		pF
$C_{res}$			67		pF
$Q_g$	$I_C = 40\text{A}, V_{GE} = 15\text{V}, V_{CE} = 1000\text{V}$		170		nC
$Q_{ge}$			19		nC
$Q_{gc}$			70		nC
$t_{d(on)}$	<b>Resistive Switching Times, <math>T_J = 25^\circ\text{C}</math></b> $I_C = 40\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 960\text{V}, R_G = 2\Omega$		36		ns
$t_r$			330		ns
$t_{d(off)}$			110		ns
$t_f$			1120		ns
$t_{d(on)}$	<b>Resistive Switching Times, <math>T_J = 125^\circ\text{C}</math></b> $I_C = 40\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 960\text{V}, R_G = 2\Omega$		46		ns
$t_r$			740		ns
$t_{d(off)}$			118		ns
$t_f$			1010		ns
$R_{thJC}$				0.19	$^\circ\text{C/W}$
$R_{thCS}$		0.15			$^\circ\text{C/W}$

Note: 1. Pulse test,  $t < 300\mu\text{s}$ , duty cycle,  $d < 2\%$ .

### TO-247PLUS-HV Outline



1 - Gate  
2 - Emitter  
3,4 - Collector

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.193	.201	4.90	5.10
A1	.114	.122	2.90	3.10
A2	.075	.083	1.90	2.10
A3	.035	.043	0.90	1.10
b	.053	.059	1.35	1.50
b1	.075	.083	1.90	2.10
c	.022	.030	0.55	0.75
D	.819	.843	20.80	21.40
D1	.638	.646	16.20	16.40
D2	.134	.146	3.40	3.70
D3	.055	.063	1.40	1.60
E	.622	.638	15.80	16.20
E1	.520	.528	13.20	13.40
E2	.118	.126	3.00	3.20
E3	.051	.059	1.30	1.50
e	.100	BSC	2.54	BSC
e1	.300	BSC	7.62	BSC
L	.732	.748	18.60	19.00
L1	.106	.118	2.70	3.00
Q	.216	.224	5.50	5.70
R	.165	.169	4.20	4.30

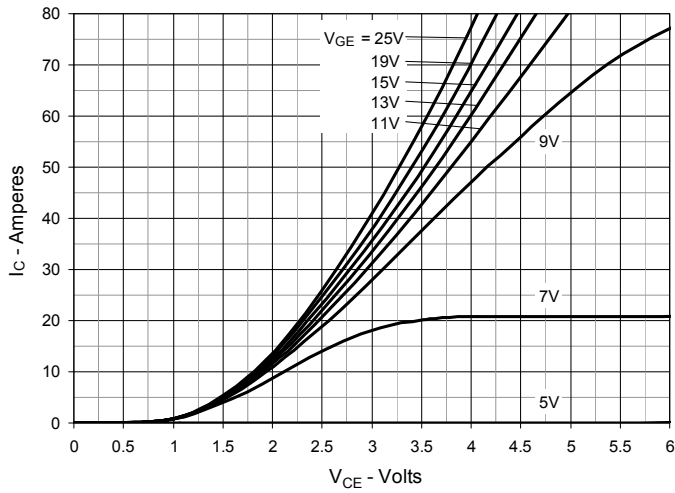
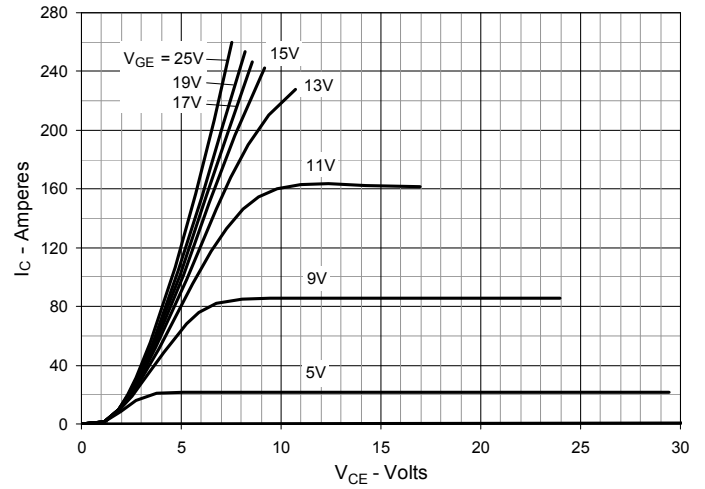
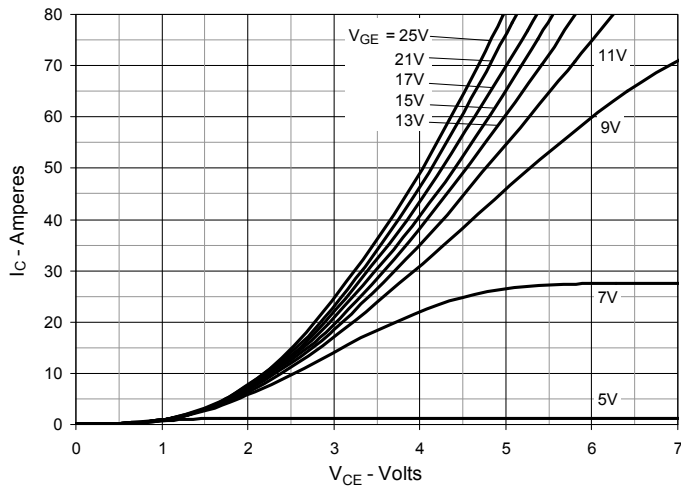
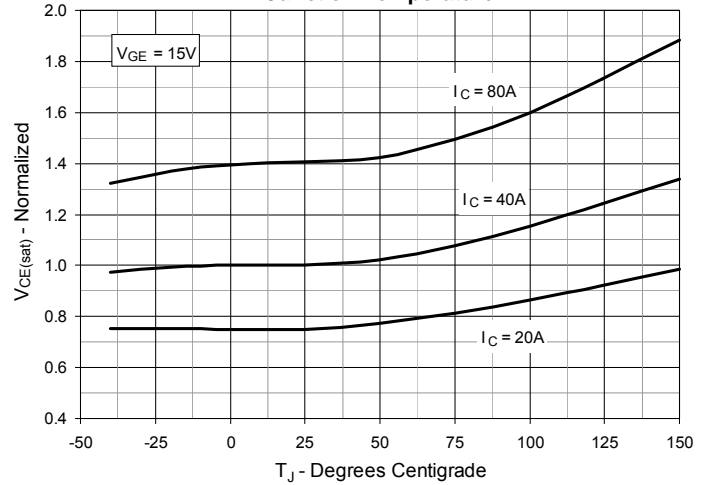
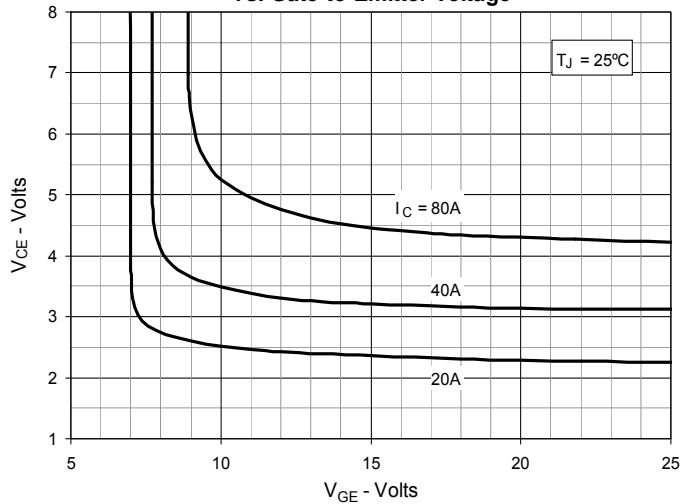
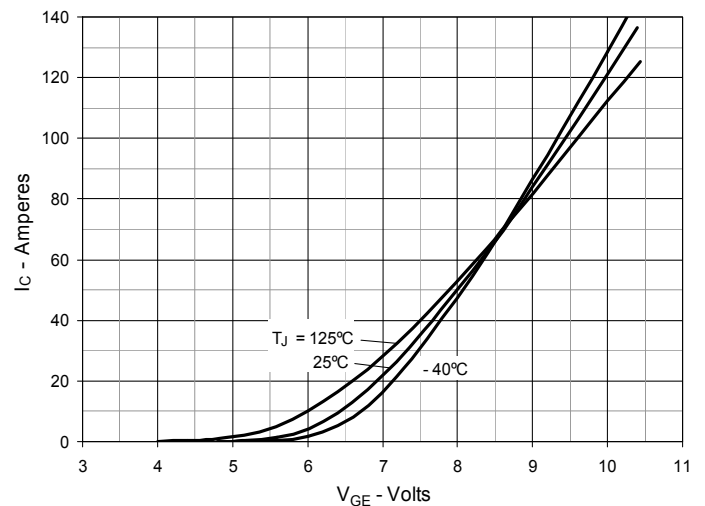
### PRELIMINARY TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

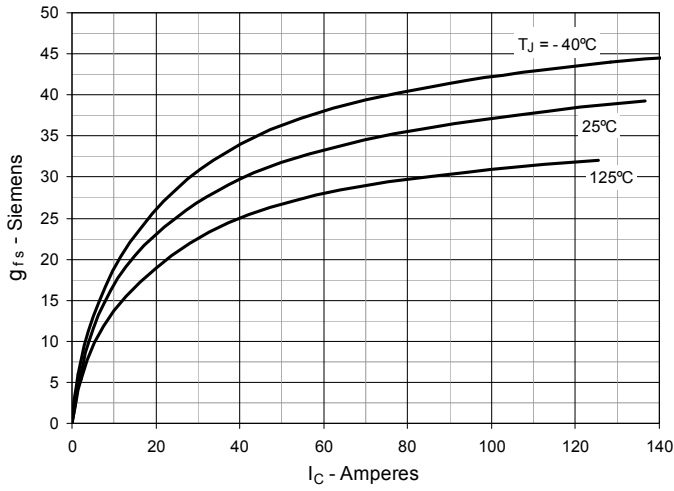
IXYS Reserves the Right to Change Limits, Test Conditions and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

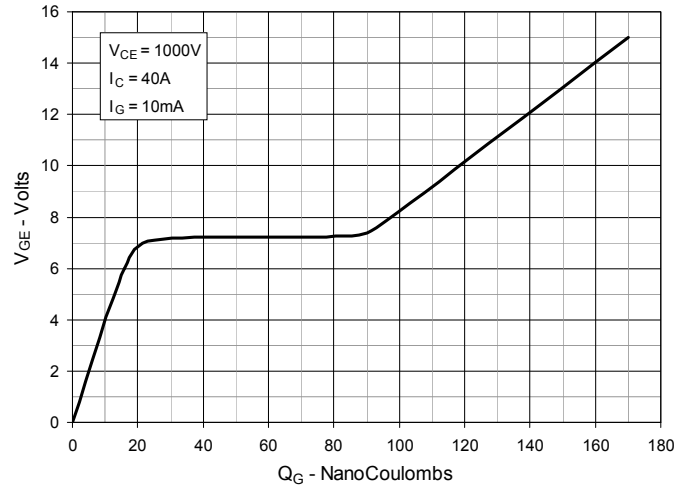
4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
4,860,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

**Fig. 1. Output Characteristics @  $T_J = 25^\circ\text{C}$** 

**Fig. 2. Extended Output Characteristics @  $T_J = 25^\circ\text{C}$** 

**Fig. 3. Output Characteristics @  $T_J = 125^\circ\text{C}$** 

**Fig. 4. Dependence of  $V_{CE(sat)}$  on Junction Temperature**

**Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage**

**Fig. 6. Input Admittance**


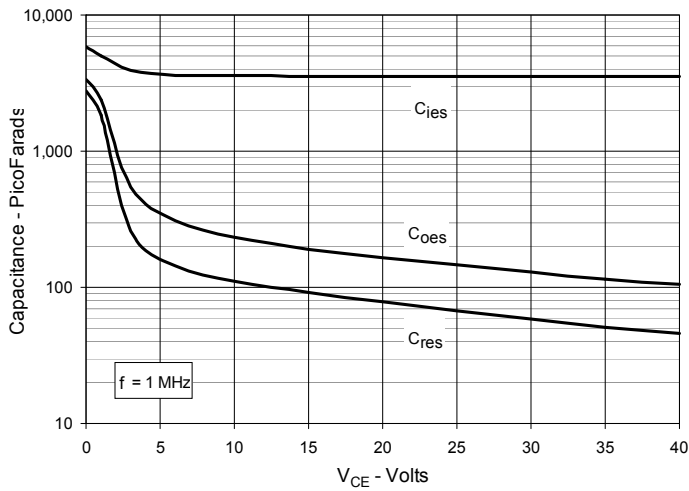
**Fig. 7. Transconductance**



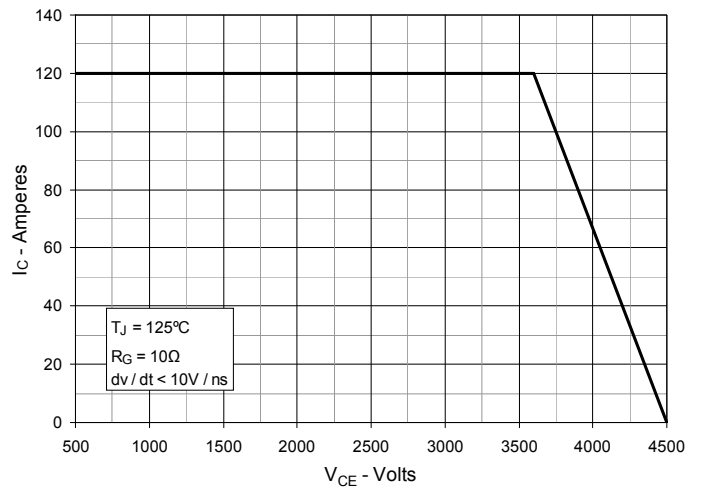
**Fig. 8. Gate Charge**



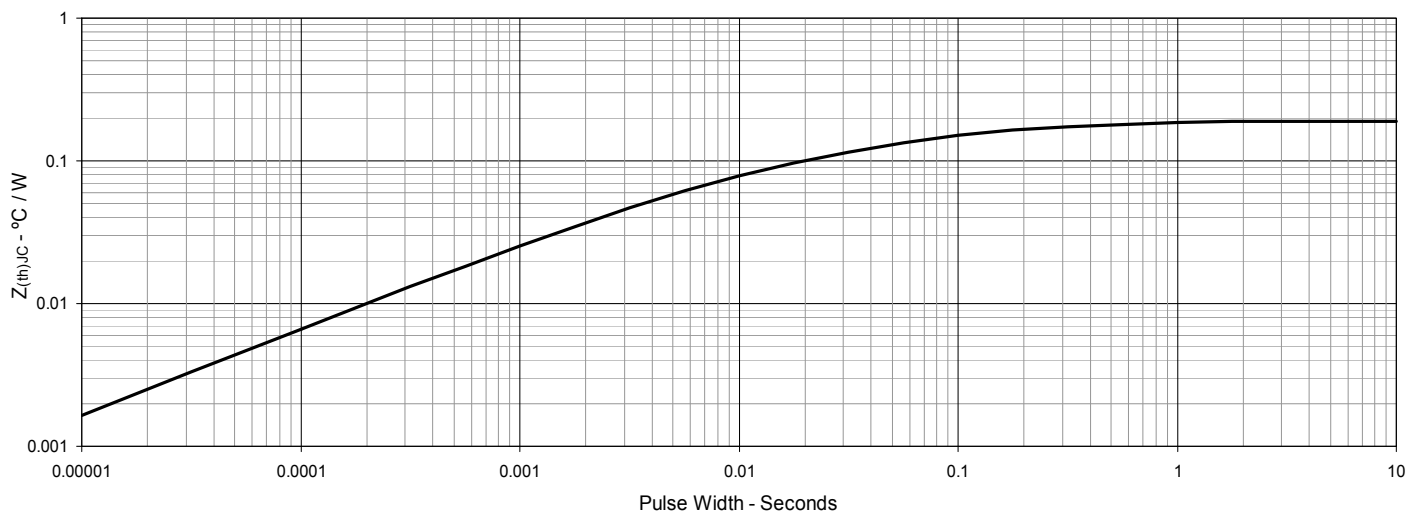
**Fig. 9. Capacitance**



**Fig. 10. Reverse-Bias Safe Operating Area**



**Fig. 11. Maximum Transient Thermal Impedance**



IXYS Reserves the Right to Change Limits, Test Conditions and Dimensions.



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